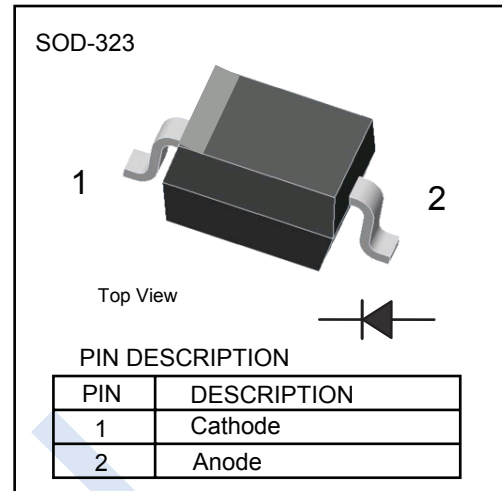


Switching Diodes

1KS1012F

■ Features

- Silicon epitaxial planar diode
- Fast switching diode

■ Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$, unless otherwise specified)

Parameter	Symbol	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	130	V
Reverse Voltage	V_R	100	
Forward continuous current	I_F	250	mA
Non-repetitive peak forward current	$t = 1\mu\text{s}$	2	A
	$t = 1\text{ms}$	1	
	$t = 1\text{s}$	0.5	
Power dissipation	P_{tot}	200	mW
Thermal resistance junction to ambient air	R_{thJA}	650	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics ($T_a = 25^\circ\text{C}$, unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse current	I_R	$V_R = 100\text{ V}$			1	μA
		$V_R = 25\text{ V}, T_J = 150^\circ\text{C}$			30	
		$V_R = 100\text{ V}, T_J = 150^\circ\text{C}$			50	
Forward voltage	V_F	$I_F = 1\text{ mA}$			0.715	V
		$I_F = 10\text{ mA}$			0.855	
		$I_F = 50\text{ mA}$			1	
		$I_F = 150\text{ mA}$			1.25	
Diode capacitance	C_D	$V_R = 0\text{ V}, f = 1\text{ MHz}$			2	pF
Reverse recovery time	t_{rr}	$I_F = I_R = 10\text{ mA}, i_R = 1\text{ mA}, R_L = 100\ \Omega$			4	ns

■ Marking

Marking	A
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Switching Diodes

1KS1012F

■ Typical Characteristics

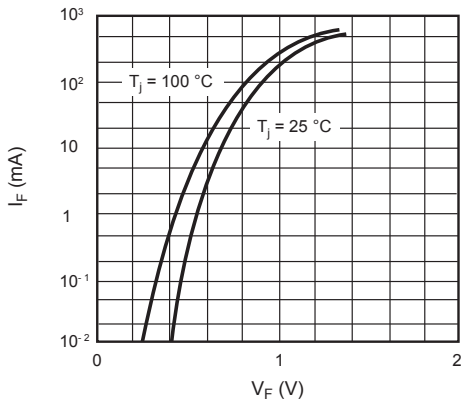


Fig. 1 - Forward Characteristics

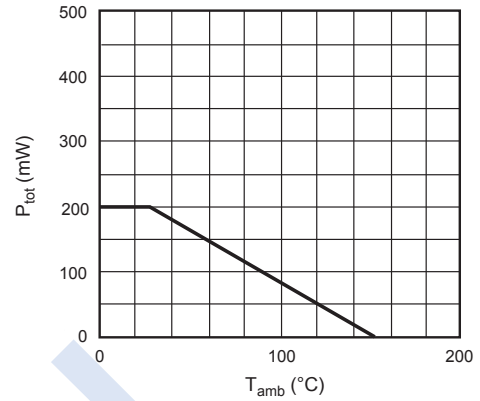


Fig. 3 - Admissible Power Dissipation vs. Ambient Temperature

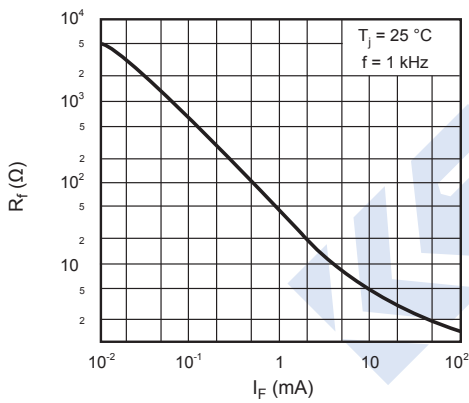


Fig. 2 - Dynamic Forward Resistance vs. Forward Current

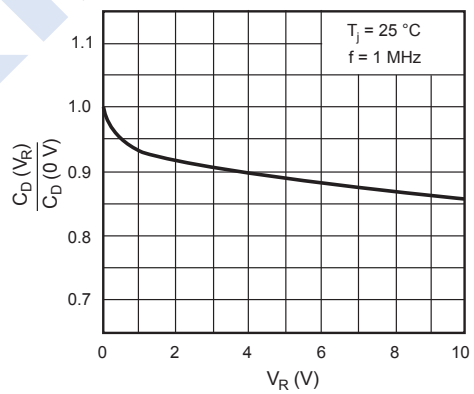


Fig. 4 - Relative Capacitance vs. Reverse Voltage

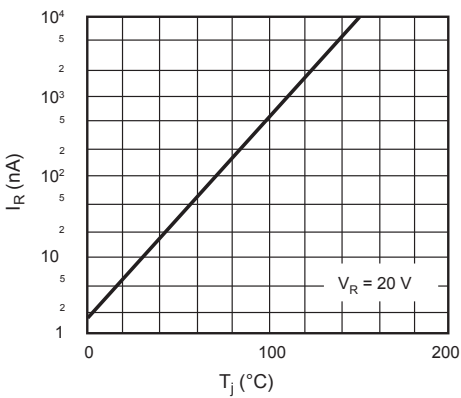


Fig. 5 - Leakage Current vs. Junction Temperature

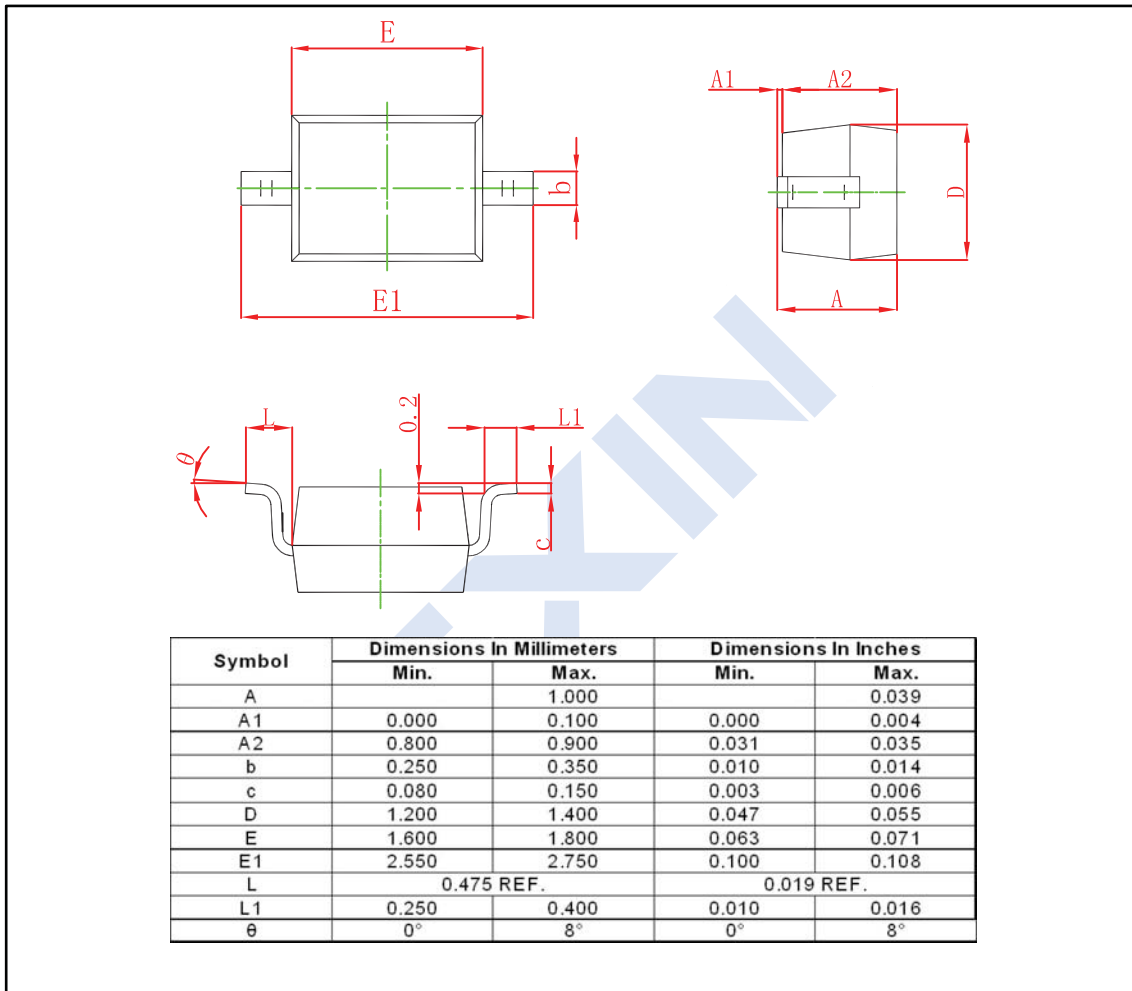
Switching Diodes

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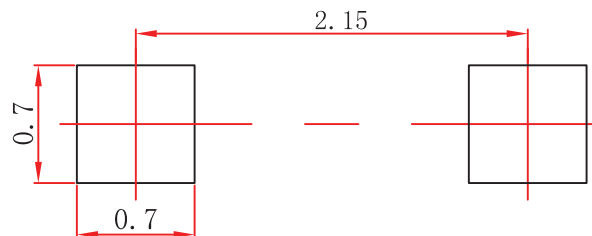
■ Package Outline Dimensions

Plastic surface mounted package; 2 leads

SOD-323



■ The Recommended Mounting Pad Size

**Note:**

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.